

[查询"SEMiX302KD"供应商](#)



SEMIX® 2s

Rectifier Diode Module

SEMiX 302KD

Preliminary Data

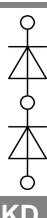
Features

- Terminal height 17 mm
- Chips soldered directly to isolated substrate

Typical Applications

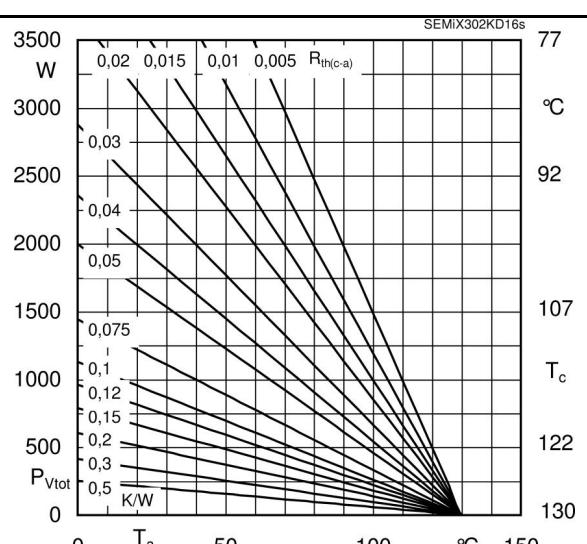
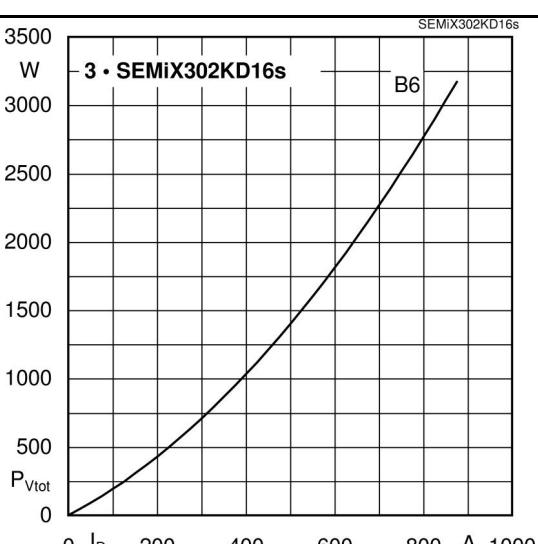
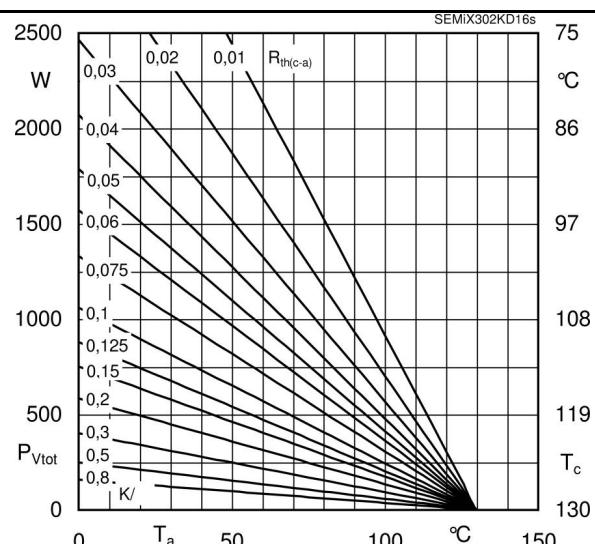
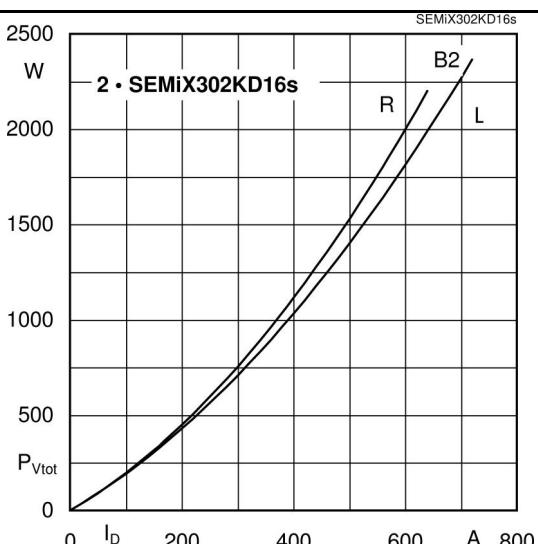
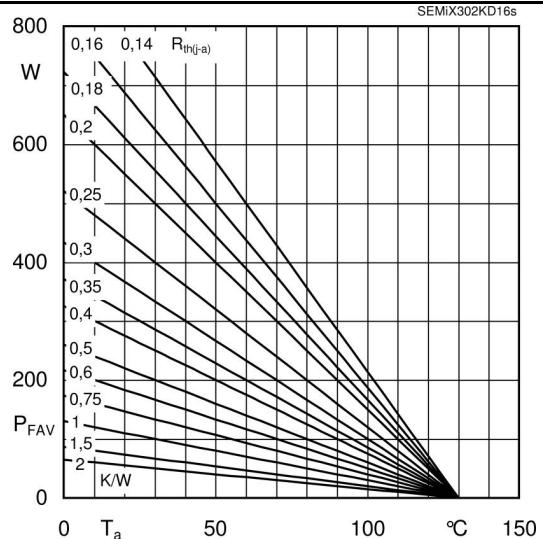
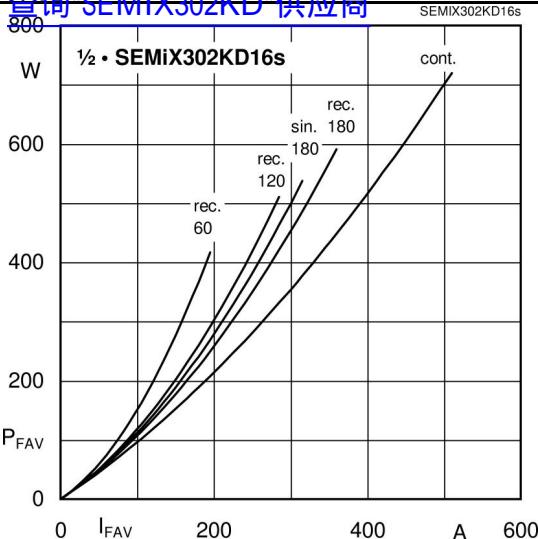
- Input Bridge Rectifier for
- AC/DC motor control
- power supply

V_{RSM} V 1700	V_{RRM} V 1600	$I_{FRMS} = 510 \text{ A}$ (maximum value for continuous operation) $I_{FAV} = 300 \text{ A}$ (sin. 180; $T_c = 85 = {}^\circ\text{C}$) SEMiX 302KD16s	
I_{FAV} sin. 180; $T_c = 85 (100) {}^\circ\text{C}$		300 (240)	A
I_{FSM} $T_{vj} = 25 {}^\circ\text{C}; 10 \text{ ms}$ $T_{vj} = 130 {}^\circ\text{C}; 10 \text{ ms}$		8500 7500	A A
i^2t $T_{vj} = 25 {}^\circ\text{C}; 8,3 \dots 10 \text{ ms}$ $T_{vj} = 130 {}^\circ\text{C}; 8,3 \dots 10 \text{ ms}$		361000 281000	A^2s A^2s
V_F $V_{(TO)}$ r_T I_{RD}	$T_{vj} = 25 {}^\circ\text{C}; I_F = 900 \text{ A}$ $T_{vj} = 130 {}^\circ\text{C}$ $T_{vj} = 130 {}^\circ\text{C}$ $T_{vj} = 130 {}^\circ\text{C}; V_{RD} = V_{RRM}$	max. 1,6 max. 0,85 max. 1,1 max. 15	V V $\text{m}\Omega$ mA
$R_{th(j-c)}$ $R_{th(c-s)}$ T_{vj} T_{stg}	per diode per module	0,091 0,045 - 40 ... + 130 - 40 ... + 125	K/W K/W °C °C
V_{isol} M_s M_t a m	AC, 50Hz; rms; 1s/1min (min./max.) (min./max.) approx.	4800 / 4000 3/5 2,5/5 5 * 9,81 220	V~ Nm Nm m/s^2 g
Case	SEMiX 2s		



KD

查询"SEMIKD302KD"供应商



查询"SEMiX302KD"供应商

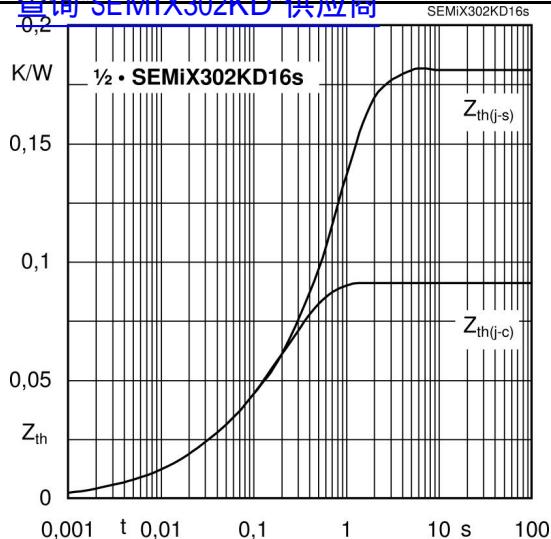


Fig. 6 Transient thermal impedance vs. time

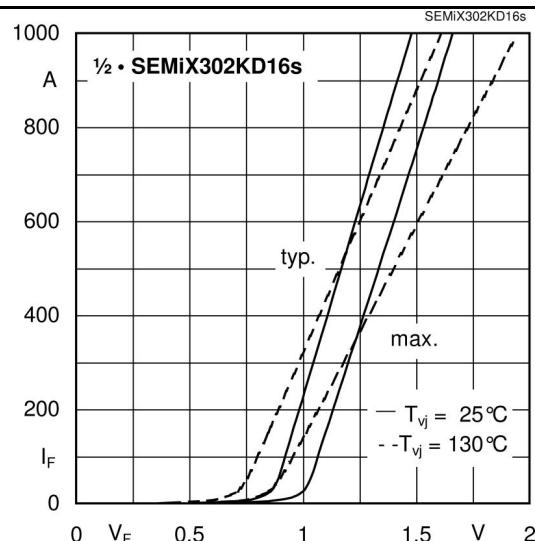


Fig. 7 Forward characteristics

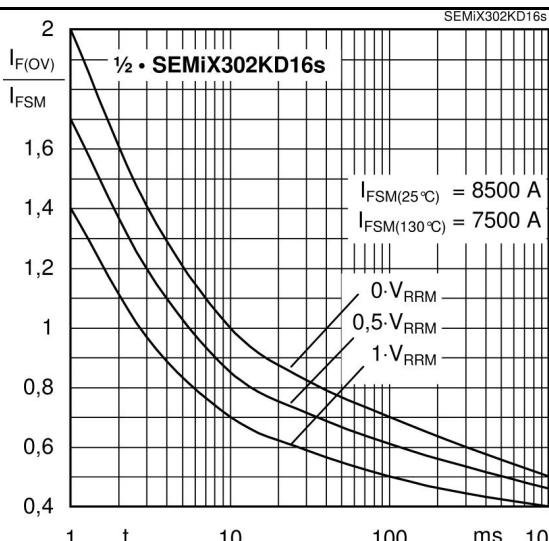
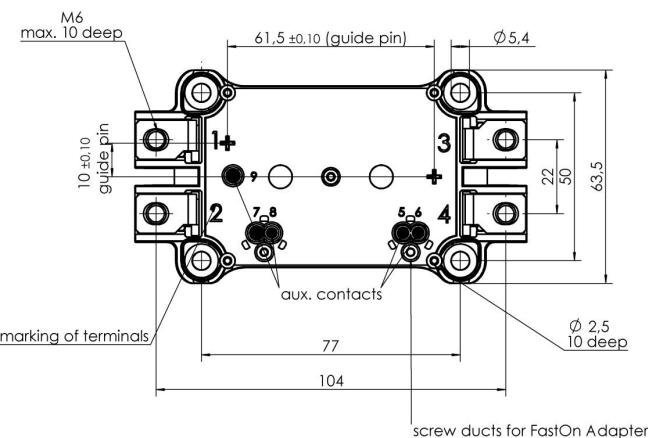
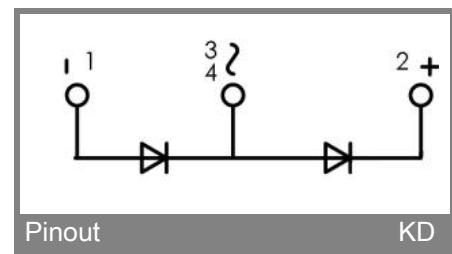
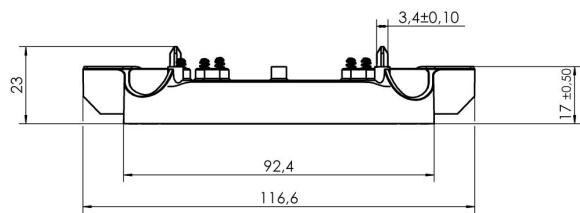


Fig. 8 Surge overload current vs. time

[查询"SEMIKRON SEMIX302KD"供应商](#)

case SEMIX2 rectifier

Dimensions in mm



Case SEMIX2s

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.